

MOSFETs Silicon N-Channel MOS ( $\pi$ -MOSIV)

# TK1P90A

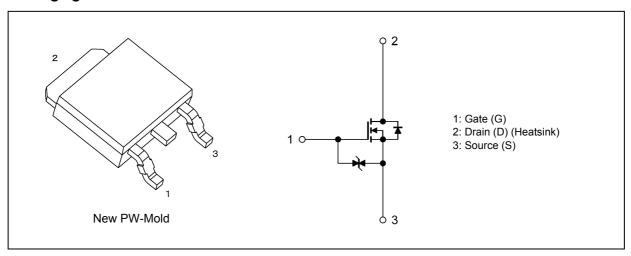
#### 1. Applications

· Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 6.7 \Omega$  (typ.)
- (2) High forward transfer admittance:  $|Y_{fs}| = 1.0 \text{ S (typ.)}$
- (3) Low leakage current:  $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 720 \text{ V)}$
- (4) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                      | Symbol   | Rating           | Unit       |    |
|--------------------------------------|----------|------------------|------------|----|
| Drain-source voltage                 |          | $V_{DSS}$        | 900        | V  |
| Gate-source voltage                  |          | $V_{GSS}$        | ±30        |    |
| Drain current (DC)                   | (Note 1) | I <sub>D</sub>   | 1          | Α  |
| Drain current (pulsed)               | (Note 1) | I <sub>DP</sub>  | 3          | ]  |
| Power dissipation $(T_c = 25^\circ)$ | °C)      | P <sub>D</sub>   | 20         | W  |
| Single-pulse avalanche energy        | (Note 2) | E <sub>AS</sub>  | 216        | mJ |
| Avalanche current                    |          | I <sub>AR</sub>  | 1          | Α  |
| Repetitive avalanche energy          | (Note 3) | E <sub>AR</sub>  | 2.0        | mJ |
| Channel temperature                  |          | T <sub>ch</sub>  | 150        | °C |
| Storage temperature                  |          | T <sub>stg</sub> | -55 to 150 |    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max  | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 6.25 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 125  |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 396 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 1 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



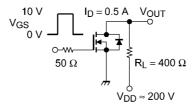
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|-----|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   |      | ±10 | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V    | _   | _    | 100 |      |
| Gate-source breakdown voltage  | V <sub>(BR)GSS</sub> | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$          | ±30 |      |     | V    |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 900 | _    | _   |      |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA     | 2.0 | _    | 4.0 |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A    | _   | 6.7  | 9.0 | Ω    |
| Forward transfer admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A    | 0.3 | 1.0  | _   | S    |

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 320  | _   | pF   |
| Reverse transfer capacitance   | $C_{rss}$        |  | _   | 10   | _   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 35   | _   |      |
| Switching time (rise time)     | t <sub>r</sub>   | See Figure 6.2.1.  | _   | 25   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 60   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 30   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 155  | _   |      |



Duty  $\leq$  1 %,  $t_W = 10 \ \mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

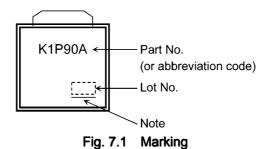
| Characteristics                                 | Symbol   | Test Condition   | Min | Тур. | Max | Unit |
|---|----------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$    | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$ |     | 13   | 1   | nC   |
| Gate-source charge                              | $Q_{gs}$ |  |     | 6    |     |      |
| Gate-drain charge                               | $Q_{gd}$ |  |     | 7    |     |      |

### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                |          | Symbol           | Test Condition                               | Min | Тур. | Max  | Unit |
|--------------------------------|----------|------------------|--|-----|------|------|------|
| Reverse drain current (DC)     | (Note 1) | I <sub>DR</sub>  | _  | _   | _    | 1    | Α    |
| Reverse drain current (pulsed) | (Note 1) | I <sub>DRP</sub> | _  | _   | _    | 3    |      |
| Diode forward voltage          |          | $V_{DSF}$        | I <sub>DR</sub> = 1 A, V <sub>GS</sub> = 0 V | _   | _    | -1.7 | V    |
| Reverse recovery time          |          | t <sub>rr</sub>  | I <sub>DR</sub> = 1 A, V <sub>GS</sub> = 0 V | _   | 550  | _    | ns   |
| Reverse recovery charge        |          | Q <sub>rr</sub>  | -dI <sub>DR</sub> /dt = 100 A/μs             | _   | 2.2  | _    | μС   |



### 7. Marking (Note)



Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

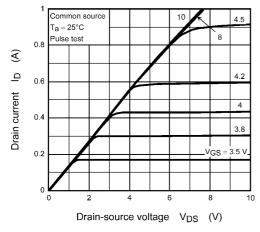


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

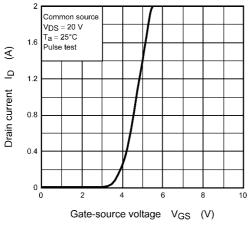


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

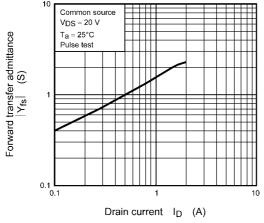


Fig. 8.5 |Y<sub>fs</sub>| - I<sub>D</sub>

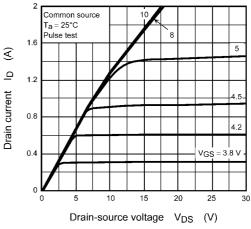


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

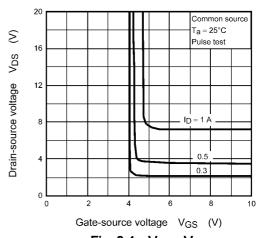


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

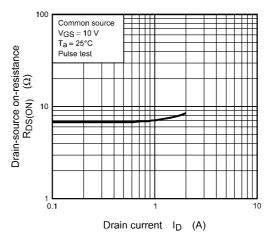


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

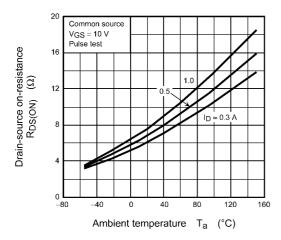


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

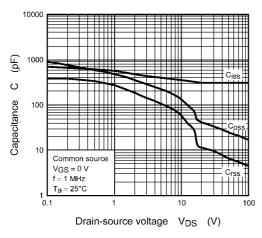


Fig. 8.9 C - V<sub>DS</sub>

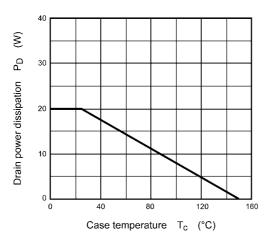


Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

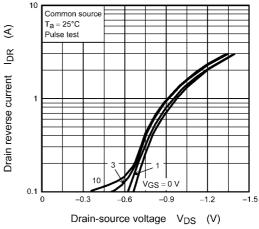


Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>

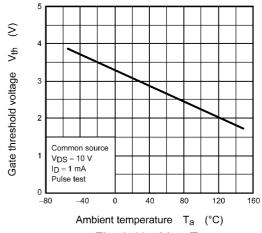


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

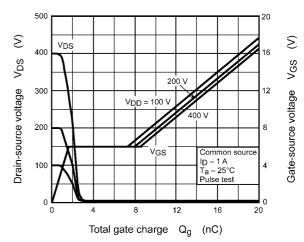


Fig. 8.12 Dynamic Input/Output Characteristics

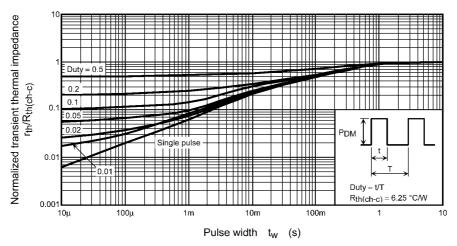


Fig. 8.13  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

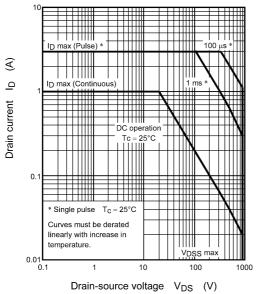


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

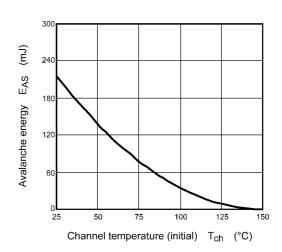


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

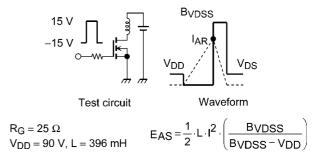


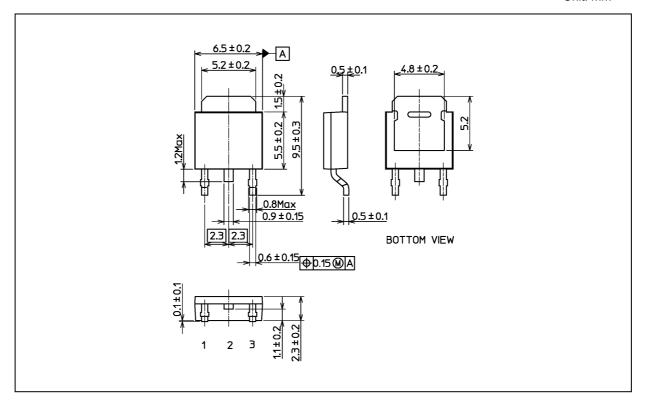
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

| Package Name(s)       |  |
|-----------------------|--|
| TOSHIBA: 2-7J1S       |  |
| Nickname: New PW-Mold |  |



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